

MEMC Datasheet

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1. Introduction

The Memory Controller (MEMC) acts as the interface between the ARM (Acorn RISC Machine) processor, Video Controller (VIDC), I/O Controllers (including IOC), Read-Only memories (ROM) and Dynamic memory devices (DRAM), providing all the critical system timing signals.

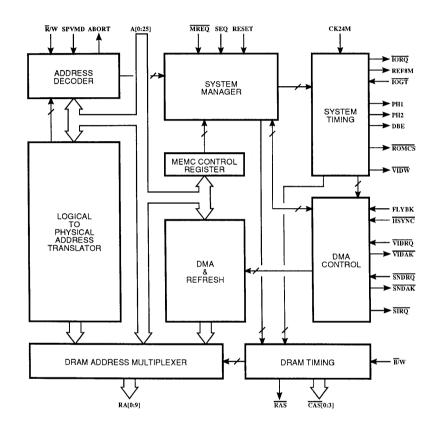
Up to 4MBytes of DRAM may be connected to MEMC, which provides all signals and refresh operations for a wide variety of standard DRAMs. A *Logical to Physical Address Translator* maps the Physical memory into a 32MByte Logical address space (with three levels of protection) allowing Virtual Memory and Multi-Tasking operations to be implemented. Fast "page mode" DRAM accesses are used to maximise memory bandwidth.

MEMC supports Direct Memory Access (DMA) read operations with a set of programmable *DMA Address Generators*, which provide a circular buffer for Video data, a linear buffer for Cursor data, and multiple buffers for Sound data.

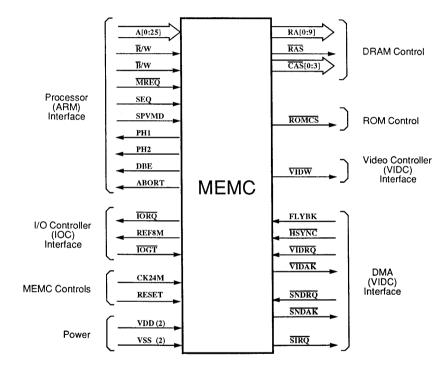
FEATURES

- Directly drives standard Dynamic RAMs
- * Supports up to 4MBytes of real memory
- * Logical to Physical address translation
- * Three protection levels supported
- Uses fast "Page mode" DRAM accesses to maximise memory bandwidth
- * Internal DMA address generators for Video, Cursor and Sound data buffers
- * Arbitrates memory between the processor and DMA.
- * Many ROM speeds supported
- Provides all critical system timing signals, including processor clocks.
- * Fabricated in CMOS for low power

2. Block Diagram



3. Functional Diagram



4. Description of Signals

Pin Numbers given for the Jedec B package

Name	Pin	Туре	Description
A[0:25]	26-10,8-1,68	IC	Processor address lines.
\overline{R}/W	62	IC	Processor Not-Read/Write. Determines the direction of data flow during processor memory accesses. (Note 1)
B/W	63	IC	Processor Not-Byte/Word. Determines whether a processor memory access is byte-wide (8-bits) or word-wide (32-bits). (Note 1)
MREQ	55	IC	Processor memory request. This signal should be set LOW if the processor will be accessing memory in the <i>next</i> processor cycle. (Notes 1,2)
SEQ	54	IC	Processor sequential access. This signal should be set HIGH if the <i>next</i> processor cycle will access an address sequential to the current address. (Note 2)
SPVMD	52	IC	Supervisor mode select. The MEMC Supervisor protection mode is selected while this line is HIGH. (Note 3)
PH1, PH2	66, 65	OC	Processor clocks. These pins drive the two phase, non-overlapping clock inputs of the ARM processor.
DBE	56	OC	Processor data bus enable. This active HIGH signal enables the processor data bus during processor write cycles, and may be inverted externally to provide an active LOW write enable for the Dynamic RAMs.
ABORT	53	OC	Processor abort. This line is driven HIGH by MEMC to inform the processor that the current memory access is illegal. (Note 1)
IORQ	59	OC	Input/Output cycle request. This signal is driven LOW by MEMC to inform the I/O controllers that an IO cycle is being requested by the processor.
REF8M	64	OC	8MHz Reference clock.
IOGT	58	IC	Input/Output cycle grant. A LOW on this input informs MEMC that the I/O Controller is ready to complete the IO cycle.
CK24M	67	IC	24MHz Master clock.
RESET	44	IC	Reset input. Active HIGH.
RA[0:9]	28-37	OT	RAM address bus. Multiplexed Row and Column address lines from MEMC which will drive up to 32 DRAMs without external buffers. (Note 4)
RAS	38	OT	Row address strobe. The HIGH to LOW transition of RAS strobes the Row address on RA[0:9] into the DRAMs. This line will drive up to 32 DRAMs without external buffers.

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CAS[0:3]	39-42	ОТ	Column address strobes. Each line controls a block of 8-bits of memory; one block for \overline{cach} byte of the 4-byte word. The HIGH to LOW transition of a $\overline{CAS}[0:3]$ line strobes the Column address on $RA[0:9]$ into the DRAMs. Each line will drive up to 8 DRAMs without external buffers.
ROMCS	60	OC	ROM chip select. This line is driven LOW when the processor accesses the Read Only Memories (ROMs).
VIDW	51	OC	Video Controller write strobe. This line is driven LOW while the processor is performing a write operation to the Video Controller.
FLYBK	45	IC	Video vertical flyback. This signal should be set HIGH while the video retrace is in progress. FLYBK is used to initialise the video and cursor DMA address pointers.
HSYNC	46	IC	Video horizontal synchronisation. Video data requests made while this signal is LOW will obtain data from the cursor data buffer. A video data request made when $\overline{\text{HSYNC}}$ is HIGH obtains data from the video data buffer.
VIDRQ	48	IC	Video data request. A LOW on this line requests a video or cursor DMA operation (depending on the sense of HSYNC).
VIDAK	50	OC	Video data acknowledge. This line is driven LOW to indicate that the requested video/cursor data is being fetched from RAM. The data should be latched on the rising edge of \overline{VIDAK} .
SNDRQ	47	IC	Sound data request. A LOW on this line requests a sound DMA operation.
SNDAK	49	OC	Sound data acknowledge. This line is driven LOW to indicate that the requested sound data is being fetched from RAM. The data should be latched on the rising edge of \$\overline{SNDAK}\$.
SIRQ	57	OC	Sound interrupt request. This line is driven LOW to request a sound service interrupt operation from the processor. \overline{SIRQ} is set LOW on reset.
VSS	27,61	PWR	Ground supply.
VDD	9,43	PWR	Positive supply.

Key to Signal Types:

IC CMOS compatible input

OC CMOS compatible output

OT TTL compatible output

PWR Power pins

See D.C. Parameters (Section 7).

NOTES:

- (1) The word "Memory" in this context refers to any device mapped into the processor's address space.
- (2) Some of the processor signals are asserted in the processor cycle preceding that in which they are used.
- (3) SPVMD is generally connected to the TRANS pin of the ARM processor.
- (4) The bit order and logic level of the RA[0:9] RAM address bus changes according to the Page size selected in MEMC. (see Appendix A)

5. General Description

5.1 Protection Modes

MEMC may be operated in three protection modes:

(i) Supervisor Mode

Supervisor mode is selected while the SPVMD input is held HIGH. This is the most privileged mode, allowing the entire memory map to be freely accessed.

(ii) Operating System Mode (OS Mode)

OS mode is selected by setting a control bit in the *MEMC Control Register* (which may only be done from Supervisor mode). OS mode is more privileged than User mode when accessing Logically Mapped RAM, but acts like User mode in all other cases.

(iii) User Mode

User mode is the least privileged of the three protection modes. Unprotected pages in the Logically Mapped RAM may be accessed when in User mode, and the ROM space may be read, but no other accesses are allowed.

All attempts to access protected addresses from an insufficiently privileged mode (User mode or OS mode) will activate the ABORT line without performing the access.

5.2 Memory Pages

MEMC treats the DRAM it controls as a set of 128 sequential *Physical Pages*. The *Page* is the fundamental unit of memory used by MEMC¹, and the *Page Size* may be selected as 4, 8 16 or 32 KBytes by programming the *MEMC Control Register*.

The page size selection affects the DRAM address multiplexer, so it is essential to choose the correct page size for the amount of memory being controlled. Table 1 shows the page size selections for most DRAM configurations. When less than 512KBytes of DRAM is connected to MEMC, a page size of 4KBytes should be used, but note that two or more Physical pages will now map onto the same address in the DRAM.

5.3 Memory Map

MEMC accepts 26 address lines from the processor, A[0:25], which are decoded as shown by the memory map in Figure 1.

5.3.1 Logically Mapped RAM (Read/Write: 0000000H - 1FFFFFFH)

The bottom 32MBytes of the memory map consists of Logically mapped RAM. MEMC treats this area of the map as a set of contiguous *Logical Pages* (there may be 8192, 4096, 2048 or 1024 Logical pages depending upon the page size selected).

	READ	WRITE	_
	ROM (High)	Logical to Physical Address Translator	3FFFFFFH
		DMA Address Generators	3800000H
	ROM (Low)	MEMC Control Register	3600000H
		Video Controller	3400000H
*	Input/Outpu	3000000H ≈ 2000000H	
*	≿ Logi Map Ra	ically oped AM	≈

NOTE: The shaded areas are only accessible while Supervisor mode is selected.

Figure 1: Processor memory map as decoded by MEMC

¹ The MEMC Page unit should not be confused with the "Page mode access" capability of Dynamic RAMS.

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		 Number of	Number of
Total amount of DRAM	 Page Size	Physical Pages	Logical Pages
OI DRAM	rage 512e		rages
 512 KBytes	 4 KBytes	 128	 8192
l 1 MByte	 8 KBytes	128	4096
 2 MBytes	 16 KBytes	1 128	 2048
 4 MBytes 	 32 KBytes 	128	1024

Table 1: Recommended Page size settings

When a Logical page is accessed, the Logical to Physical Address Translator attempts to convert the Logical Page Number to a Physical Page Number. Provided that the mapping exists, and the request is being made in a sufficiently privileged mode, the appropriate Physical page will be accessed. If the mapping does not exist, or the access is made with insufficient privilege, MEMC will signal the processor by setting the ABORT line HIGH, and the DRAM will not be activated.

The Logical to Physical mapping and protection status of each Logical page is undefined at power on, but may be programmed at any time by writing to the Logical to Physical Address Translator.

5.3.2 Physically Mapped RAM (Read/Write: 2000000H - 2FFFFFFH)

The Physically mapped RAM occupies 16MBytes of the memory map, and may only be accessed when Supervisor mode is selected. The 128 *Physical pages* appear sequentially in this area of the map, with the RAM image being repeated after every 128th page (so that, with a page size of, say, 8KBytes, the entire 1MByte of RAM would occur 16 times throughout this area).

5.3.3 Input/Output Controllers (Read/Write: 3000000H - 33FFFFFH)

This area of the map is reserved for I/O Controllers (including IOC). When a Supervisor mode access is made in this memory range, MEMC asserts \overline{IORQ} (IO cycle request), and stops the processor clocks. The IO cycle terminates after both \overline{IORQ} and \overline{IOGT} are seen LOW on the rising edge of REF8M.

NOTE: Care must be taken not to access a non-existent I/O Controller, otherwise MEMC will wait indefinitely for an active $\overline{\text{IOGT}}$ signal that never appears, and the processor will stop until **RESET** is asserted.

5.3.4 ROM (Read: 3400000H - 3FFFFFFH)

Read Only Memory may be read freely from any protection mode. The ROM space is divided into two areas:

- (i) Low ROM (4MBytes from 3400000H to 37FFFFFH)
- (ii) High ROM (8MBytes from 3800000H to 3FFFFFFH)

The two ROM areas are distinguished only by the fact that each may be programmed to operate at its own speed. This would allow the High ROM area to contain fast system ROMs, with slower applications ROMs in the Low ROM area.

The ROM speeds default to the slowest setting when RESET is asserted, and may be altered by reprogramming the MEMC Control Register.

5.3.5 Video Controller (Write: 3400000H - 35FFFFFH)

A write operation made anywhere in the Video Controller space (while MEMC is in Supervisor mode) activates the $\overline{\text{VIDW}}$ output from MEMC.

5.3.6 Address Generators & Control Register (Write: 3600000H - 37FFFFFH)

This address space decodes to some of MEMC's internal registers. The *DMA Address Generators* supply the Physical RAM address used to obtain data during Video, Cursor and Sound Direct Memory Access operations, and the *MEMC Control Register* controls a number of the functions of MEMC.

The processor data bus is not connected to MEMC; instead, the internal registers are programmed by encoding the data in the address bus, and performing a write operation with MEMC in Supervisor mode.

5.3.7 Logical to Physical Address Translator (Write: 3800000H - 3FFFFFFH)

The mapping of *Logical pages* to *Physical pages*, and protection mode associated with each mapping, may be controlled by programming the *Logical to Physical Address Translator*. The Address Translator is programmed by encoding data in the address lines, and performing write operations in Supervisor mode to this area of the memory map.

5.4 Effect of Reset

When the RESET line is taken HIGH, MEMC initialises to the following state:

- Memory Map

The ARM processor starts executing code from location 0000000H after **RESET** goes inactive. To ensure that the processor always finds valid code at this location (which is normally Logically mapped RAM), MEMC continually enables ROM.

To restore the normal memory map, the processor must first perform a memory access with the address lines A[25] and A[24] both LOW, and then perform a memory access with address line A[25] HIGH. These conditions are satisfied when the processor starts executing instructions from location 0000000H, and later jumps to the normal ROM space.

Note that a processor write operation should not be performed while ROM is continually enabled, or a data bus clash will occur.

ROM access times

The ROM access times for both High and Low ROM are reset to 450ns.

- Page sizes

The DRAM page size defaults to 4KBytes.

- Operating System mode

The Operating System mode is disabled.

Direct Memory Access (DMA) operations

Sound DMA operations are disabled. Video and Cursor DMA operations are unaffected by reset.

Sound Interrupts

The Sound Interrupt pin, STRQ is set LOW. The interrupt may be removed by initialising the Sound DMA buffers in the DMA Address Generators. (see Section 6.7.3)

- IO cycle request

The \overline{IORQ} line is held HIGH during reset to avoid accidentally triggering an I/O Controller if the processor generates spurious addresses while **RESET** is active.

- Test mode

The *Test mode* is disabled by **RESET**. Test mode is only used for functional testing of MEMC out of the system.

6. Functional Description

6.1 Introduction

6.1.1 Access Times

A number of devices appear in the processor memory map:

- Dynamic Random Access Memory (DRAM)
- Read Only Memory (ROM)
- Input/Output Controllers
- Video Controller
- MEMC internal registers:
 - (i) MEMC Control Register
 - (ii) DMA Address Generators
 - (iii) Logical to Physical Address Translator

These devices have very different access times, ranging from 125ns for DRAMs in page-mode to over 1μ s for handshake driven IO cycles. MEMC synchronises the processor with the device it is accessing by stretching the processor clocks, PH1 and PH2.

The processor is the default user of the data bus and memory. However, DMA (Direct Memory Access) and refresh operations require control of the DRAM and data bus, so MEMC disables the processor temporarily during these operations by tri-stating the processor data bus (using **DBE**), and holding the processor clocks.

6.1.2 N-cycles and S-cycles

MEMC uses the *page mode access* capability of DRAMs, where, once a row address has been strobed into the DRAM, any column in that row may be accessed merely by strobing in the new column address.

This facility is used whenever a number of sequential addresses in the DRAM are to be accessed (either by the processor or during a DMA operation). The first memory access in the sequence is a Non-sequential memory cycle (where both the row and column addresses are strobed to the DRAMs). The subsequent memory accesses are Sequential memory cycles (where the previous row address is held, and only the column address is strobed to the DRAMs).

Sequential memory cycles may also be used with nibble-mode ROMs, where the access time is reduced if only the low order address bits are changed.

The terms N-cycle and S-cycle refer to Non-sequential and Sequential accesses in DRAM or nibble-mode ROM.

6.2 Processor (ARM) Interface

6.2.1 Processor cycles

There are two basic types of processor operation:

(i) Memory access cycles

Where the processor accesses a device in its address space.

(ii) Internal cycles

Where the processor is performing an internal operation, and so does not access any external devices.

6.2.2 Processor signals

- Address bus {A[0:25]}

The processor address bus is decoded by MEMC to give the processor access to the various devices.

Much of the processor memory map is only accessible while MEMC is in Supervisor mode (which is selected by taking the SPVMD line HIGH).

- Memory request { MREQ}

This signal determines whether the next processor cycle will be a memory access or internal cycle.

- Not-Read/Write { R/W}

Determines the direction of data flow during processor memory access cycles. This signal is ignored during processor internal cycles.

Not-Byte/Word { B/W}

Selects a byte (8-bit) or word (32-bit) data transfer during processor memory access cycles. A byte access to Physically and Logically Mapped RAM only enables the appropriate 8-bit *block* of DRAMs. ROM accesses always return a word quantity, regardless of the state of $\overline{\mathbf{B}}/\mathbf{W}$. This signal is ignored during processor internal cycles.

Sequential access (SEQ)

A HIGH on this line indicates that the processor will generate a sequential address during its next cycle. MEMC uses SEQ to determine whether a fast S-cycle may be used during the next DRAM or nibble-mode ROM access.

Supervisor mode {SPVMD}

A HIGH on this line puts MEMC into Supervisor mode, allowing the processor to access restricted areas of the memory map.

6.2.3 Processor controls

- Processor clocks {PH1, PH2}

MEMC provides the processor with two non-overlapping clocks, PH1 and PH2. Memory access cycles are nominally 250ns long, (with PH1 HIGH for approx 175ns, and PH2 HIGH for approx 55ns), but the following exceptions apply:

(i) Sequential DRAM & nibble-mode ROM accesses

DRAM and nibble-mode ROM S-cycles only take 125ns to complete, so the processor is given an 8MHz clock while S-cycles are in progress (see Section 8.4).

(ii) ROM accesses

ROM access times vary from 450ns to 200ns. PH1 is held HIGH long enough to meet the ROM access time requirement. (see Section 8.5)

(iii) IO cycles

IO cycles take a variable length of time to complete. During the longer IO cycles, the processor is suspended by holding PH2 HIGH until the I/O Controller is ready to complete the cycle. Suspending the processor during its PH2 phase allows the IO cycle to be completed quickly when the I/O Controller is ready.

(iv) DMA and refresh operations

DMA and refresh operations have priority over most processor memory access cycles (S-cycles are uninterruptable). A processor memory access is suspended during DMA and refresh operations by disabling the processor data bus drivers (using DBE), and holding the PH1 clock HIGH until the operation has finished. The processor then continues with its delayed memory access (unless another DMA/refresh operation is pending).

DMA and refresh operations may also occur during long IO cycles. In this case, the IO cycle is delayed until the DMA/refresh operation completes.

Internal cycles are always 125ns long, with PH1 and PH2 each HIGH for approx 55nS.

- Data bus enable {DBE}

Enables the processor data bus during processor write cycles. This signal may also be inverted externally, and used as a DRAM write enable signal.

Memory access abort {ABORT}

Warns the processor that the requested access is illegal (either because an attempt was made to access a protected address while MEMC was in an insufficiently privileged mode, or an access to a non-existent Logical page was attempted).

6.3 Dynamic RAM (DRAM) Interface

MEMC interfaces directly to most standard Dynamic RAMs, providing a 10-bit multiplexed RAM address bus, RA[0:9], a row address strobe, RAS, and a set of four column address strobes, CAS[0:3].

6.3.1 Byte and Word accesses

The DRAM is divided into four blocks of eight bits, with $\overline{CAS}[0]$, $\overline{CAS}[1]$, $\overline{CAS}[2]$ and $\overline{CAS}[3]$ each controlling a block ($\overline{CAS}[0]$) is the least significant block, and $\overline{CAS}[3]$ is the most significant).

The processor Byte/Word select line, \overline{B}/W , selects whether a whole word (32-bits) or a single byte (8-bits) is to be read from or written to DRAM. During a word access, all four blocks are activated, allowing the full 32-bits to be accessed. During a byte access, the two least significant address bits, A[0:1], select one of the 8-bit blocks to be activated, and only the appropriate eight bits are read from or written to the DRAMs.

6.3.2 DRAM Configurations

The Page Size setting (in the MEMC Control Register) controls how the DRAM address is presented on the RAM address bus, RA[0:9], as shown in Table 2.

Total amount of RAM	 Page Size setting	 Co 	Typical nfiguration	 Row & Column address presented on	 Bank Select
 256 KBytes 	 4KBytes 	 8 32	64Kx4 DRAM 64Kx1 DRAM	 RA[0:7] 	
512 KBytes	 4KBytes	1 16	64Kx4 DRAM	 RA[0:7]	RA[8]
1 MByte	 8KBytes 	8	256Kx4 DRAM 256Kx1 DRAM	 RA[0:8] 	
2 MBytes	 16KBytes	16	256Kx4 DRAM	 RA[0:8]	 RA[9]
4 MBytes 	 32KBytes 	8 32 	1Mx4 DRAM 1Mx1 DRAM	 RA[0:9] 	 -

Table 2: Dynamic RAM address bus configurations

NOTES:

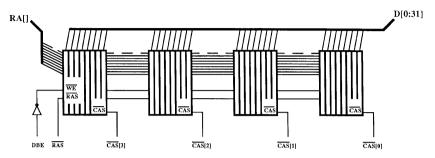
- (i) The RA[0:9] lines are derived from the processor address bus, the Logical to Physical Address Translator and the DMA Address Generators by passing the lines through the DRAM Address Multiplexer, which inverts and re-orders the address bits. See Appendix A.
- (ii) When only 256KBytes are connected to MEMC (8 off 64Kx4 or 32 off 64Kx1 DRAMs), the Bank select address bit, RA[8] is ignored by the DRAMs, so Physical pages 64-127 map onto Physical pages 0-63.

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Chapter 6

There are three basic Dynamic RAM configurations as follows:

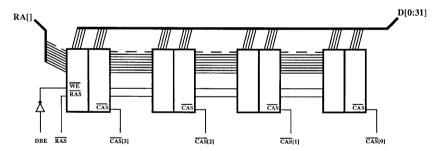
(1) Thirty-two 64Kx1, 256Kx1 or 1Mx1 DRAMs



This configuration splits the thirty-two 1-bit wide DRAMs into four blocks of eight bits. Each 8-bit block is controlled by one of the $\overline{CAS}[0:3]$ lines, allowing independent access to any of the byte-wide blocks.

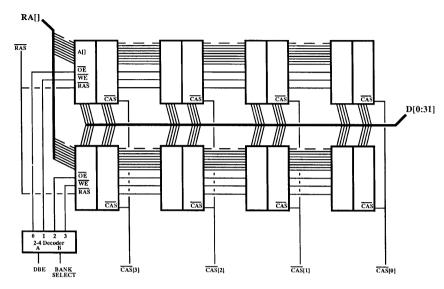
The DRAM write-enable line is derived by inverting the DBE signal from MEMC. The RAM address bus, RA[0:9], and RAS strobe are routed to all the DRAMs.

(2) Eight 64Kx4, 256Kx4 or 1Mx4 DRAMs



This configuration is essentially the same as that used for the 1-bit wide DRAMs. In this case, only eight chips are required for the full 32-bit data bus.

(3) Sixteen 64Kx4 or 256Kx4 DRAMs



The sixteen chips are configured as two banks of eight 4-bit wide DRAMs in parallel. One of the RAM address bits is used as a bank select line (valid at the same time as the Column addresses).

NOTE: A 2-4 Decoder (with active LOW outputs) is used to derive an output-enable and writeenable signal for each bank. This ensures that only the one bank is activated during any DRAM access.

6.3.3 DRAM cycles

There are three main types of DRAM accesses as follows:

- (i) Processor access {fetching instructions and reading/writing data}
- (ii) DMA operation {fetching Video, Cursor or Sound data}
- (iii) Refresh operation

MEMC uses the page mode access capability of DRAMs, performing sequential accesses (S-cycles) where possible.

Processor accesses

MEMC monitors a processor signal, SEQ, which indicates that the next processor access will be sequential.¹

If the SEQ signal is LOW in the processor cycle preceding a DRAM access (SEQ is a pipelined signal), an N-cycle DRAM access will be used.

Subsequent DRAM accesses will use S-cycles, provided that the SEQ signal is HIGH in the preceding cycle.

DMA operations may not interrupt the processor if it is about to perform an S-cycle memory access, so the maximum number of consecutive S-cycles is restricted to three. This limits the worst case DMA latency, whilst retaining the improvement that S-cycles bring. An N-cycle is forced under either of the following conditions:

- The processor SEQ signal was LOW in the preceding cycle, indicating that this access would not be to a sequential address.
- (ii) The processor address lines A[2] and A[3] were both HIGH in the preceding cycle. This restricts the maximum number of consecutive S-cycles to three.

MEMC includes an optimisation for Non-sequential memory accesses that follow an internal processor cycle. During internal cycles, the ARM processor outputs an address, and sets SEQ HIGH if the address will be valid in the next cycle (see Figure 2).

In an internal cycle preceding a processor memory access, the MREQ line will be set LOW. When MEMC sees SEQ HIGH, MREQ LOW and a valid DRAM address on A[0:25] during an internal cycle, it starts a DRAM N-cycle immediately, effectively overlapping the internal cycle with the first half of an Non-sequential cycle. The processor DRAM access can then complete with a DRAM S-cycle, as the row address was strobed in during the internal cycle. This special operation does not occur if the DRAM address has both A[2] and A[3] set HIGH (this is a consequence of the multiple S-cycle limiting logic).

DMA operations

DMA operations always fetch four words (sixteen bytes) of data sequentially from the DRAMs. Thus, DMA operations are composed of an N-cycle read followed by three S-cycle reads.

Refresh operations

 \underline{A} refresh operation is effectively a single N-cycle DRAM read operation, with the exception that the $\overline{CAS}[0:3]$ lines are not strobed LOW, so the data bus is not driven.

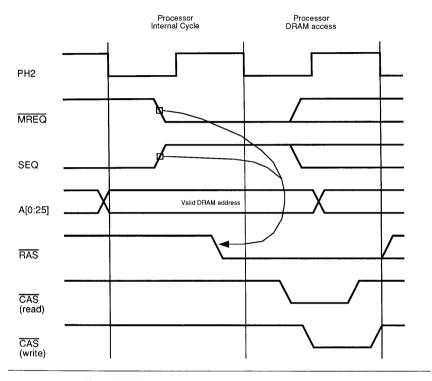


Figure 2: Optimisation for DRAM accesses following Internal cycles

6.3.4 DRAM Timing

Timing diagrams for DRAM operations are given in Section 8.4.1, Section 8.4.2 and Section 8.8.2.

The CAS[0:3] strobes are generated early in read operations, and late in write operations to improve setup and hold times on the data bus. If an ABORT is generated during an N-cycle, the RAS strobe will be activated as usual, but the CAS[0:3] signals are suppressed for this and any subsequent S-cycles, effectively disabling the DRAM.

NOTE: MEMC uses the SEQ to detect sequential accesses, and does not perform its own check on the address bus. If the SEQ signal is asserted incorrectly, the wrong memory page may be accessed.

Functional Description

6.4 Read Only Memory (ROM) Interface

To give the ROM as long as possible to access its data, the ROM chip select signal from MEMC, ROMCS, is driven LOW at the start of every processor memory access (except S-cycles), and only disabled when the processor address lines have been decoded as addressing another part of the memory map.

The ROM area of the processor memory map is divided into two sections, High ROM and Low ROM. The ROM access time in each area may be independently programmed through the *MEMC Control Register*. Four ROM access times are programmable:

- (i) 450ns
- (ii) 325ns
- (iii) 200ns
- (iv) 200ns with 60ns nibble-mode

When a ROM cycle is performed, the processor clocks are stretched as necessary to match the ROM access time.

6.5 MEMC Control Register

The MEMC Control Register is a programmable register that controls some of the functions of MEMC. The parameters are encoded into the processor address lines, as shown in Figure 3, and transferred to the Control Register by performing a write operation to the appropriate address whilst MEMC is in Supervisor mode.

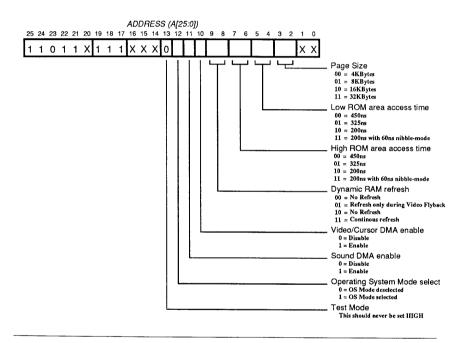


Figure 3: Programming the MEMC Control Register

Chapter 6

The following functions of MEMC are programmable:

- Logical and Physical Page size

The Logical and Physical page size must be set to correspond to the type of DRAM connected to MEMC. Page sizes of 4KBytes, 8KBytes, 16KBytes or 32KBytes may be selected.

A default Page size of 4KBytes is selected when RESET is asserted.

ROM Access Times

ROM access times of 450ns, 325ns, 200ns or 200ns with 60ns nibble-mode may be selected for each of the two ROM areas (High ROM and Low ROM).

The ROM access time in both High and Low ROM areas defaults to 450ns when RESET is asserted.

- Refresh Operations

Video DMA operations address DRAM locations sequentially at regular intervals, effectively refreshing DRAM, but video DMA operations are normally suspended during flyback.

For high resolution displays, the flyback time is short enough to ensure that the DRAM refresh period is not exceeded.

Broadcast standard displays have longer flyback times, and extra DRAM refresh must be provided during flyback to retain DRAM integrity.

When no Video DMAs are requested, all refresh operations must be generated by MEMC.

To cover these requirements, three modes of refresh operation are available:

(i) Continous refresh

A refresh operation is attempted every 4µs. The refresh operation uses the *DMA Video pointer* as the refresh address source, incrementing the pointer after use. As this effectively scrambles the *DMA Video pointer*, this mode should never be selected while a Video display is being generated.

(ii) Refresh only during Video flyback

A refresh operation is attempted every 4µs while **FLYBK** is HIGH. This mode should be selected when a broadcast standard Video display is being generated.

(iii) No refresh

This mode of operation disables refresh entirely, relying on Video DMA operations to refresh the DRAM.

Refresh operations take a single N-cycle. The processor clocks are halted during the operation (unless the processor is executing internal cycles) to ensure that the <u>processor</u> does not try to use the DRAM, and the refresh address is strobed into the DRAMs using the \overline{RAS} line.

The refresh address is provided using the DMA Video pointer, which is incremented after every refresh operation.

Refresh operations have a lower priority than DMA operations and will be delayed if a DMA operation is in progress when the refresh is attempted.

NOTE: There is no default setting for refresh operations, so the system software must turn on some form of refresh before using the DRAM. As neither the Video DMA enable bit nor the refresh mode is affected by RESET the Video Display may be maintained over a system reset.

- Direct Memory Access (DMA) control

The Video/Cursor and Sound DMA operations may be enabled or disabled as required.

Sound DMA operations are disabled when RESET is asserted.

Video/Cursor operations are unaffected by RESET.

- Operating System Mode

When Operating System mode is enabled, the processor may access certain protected Logical pages in the *Logically Mapped RAM* space. As with all *MEMC Control Register* parameters, Operating System mode may only be changed while MEMC is in Supervisor mode.

Operating System mode is disabled when RESET is asserted.

- Test Mode

Test mode reconfigures MEMC to a known state for functional testing of the chip out of the system. Test mode must **NEVER** be enabled during normal operation, as it removes all sources of DRAM refresh, and halts the processor.

Test mode is disabled when RESET is asserted.

6.6 Logical to Physical Address Translator

The physical RAM is divided into 128 *Physical pages*, which the processor may either access directly through the *Physically Mapped RAM* area of the memory map, or indirectly through the *Logically Mapped RAM* area (which is composed of *Logical pages*). The *Logical to Physical Address Translator* controls the mapping of Logical pages to Physical pages, and allows a level of protection to be attached to each Logical page.

6.6.1 Page Protection Levels

The Logical page Protection Levels available are shown in Figure 4.

			Page Prote (PPL	ection Level [1:0])	
		00	01	10	11
	Supervisor	Read/Write	Read/Write	Read/Write	Read/Write
MEMC Protection Mode	Operating System	Read/Write	Read/Write	Read	Read
	User	Read/Write	Read		

Figure 4: Logical page Protection Levels

The protection level is specified by two bits, but two of the four patterns are identical, so only three protection levels are available:

- The lowest protection level (PPL[1]=0,PPL[0]=0) allows the Logical page to be freely accessed when MEMC is in any protection mode.
- (ii) The medium protection level (PPL[1]=0,PPL[0]=1) allows the Logical page to be freely accessed when MEMC is in Supervisor or OS mode, but prevents write operations from User mode.
- (iii) The highest protection level (PPL[1]=1,PPL[0]=X) allows the Logical page to be accessed when MEMC is in Supervisor mode, prevents write operations from OS mode, and disallows any User mode accesses.

If the protection mode of MEMC is insufficently privileged to access a protected page, or the logical page being accessed has no physical page mapping, the ABORT line will be taken HIGH to inform the processor that the memory operation was aborted, and the $\overline{CAS}[0:3]$ lines will be held HIGH to ensure the DRAM is not activated.

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6.6.2 Address Translator mapping

The Address Translator consists of a 128 entry lookup table. Each of the 128 entries corresponds to a Physical page number. A Logical to Physical mapping is made by storing a Logical page number in the appropriate entry. Each entry also contains the two bit Page Protection Level.

When the processor accesses Logically Mapped RAM, the Logical page number is applied to all 128 table entries simultaneously. If one of the entries contains the required Logical page number, and the current operating mode of MEMC is sufficiently privileged to overcome the Page Protection Level, the appropriate Physical page (the number of the entry that matched) is output to the DRAMs.

If none of the entries match the requested Logical page, or a match is found but the Page Protection Level is too high, the ABORT line is set HIGH, and the DRAM is not activated.

NOTE: It is possible to store the same Logical page number in more than one entry; however, when that Logical page is accessed, those entries will all match, and an invalid Physical page number will result.

6.6.3 Programming the Address Translator

The Address Translator is programmed by specifying the Physical and Logical page numbers that are to be associated and the required protection level.

As MEMC does not monitor the processor data bus, the information is encoded into the address lines, and conveyed to the Address Translator by performing a write operation to the calculated address (with MEMC in Supervisor mode). Note that the page size not only affects the number of Logical pages available, but also changes the bit order in which the Logical and Physical Page numbers are specified. Diagrams showing how the information is encoded into an address for each of the four possible page sizes are shown in Figure 5.

NOTES:

- (i) The Address Translator is undefined on power up.
- (ii) The Address Translator mappings are not affected by reset, but are effectively scrambled if the page size is changed.
- (iii) Only one Physical page should be mapped to any given Logical page.

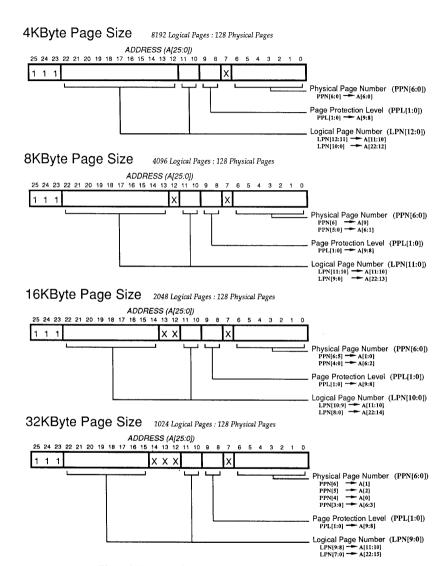


Figure 5: Programming the Logical to Physical Address Translator

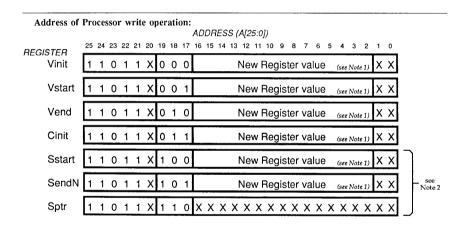
6.7 DMA Address Generators

The DMA Address Generators automatically generate addresses during a DMA service. These DMA addresses are used to obtain 16 bytes of data from the DRAM (all DMA data must be aligned on 16 byte boundaries). The data is obtained using four DRAM accesses; each access supplies one word (four bytes) of data which may be latched from the data bus when the appropriate DMA acknowledge line is strobed.

The DMA Address Generators implement three sets of buffers:

- (i) Video Buffer
- (ii) Cursor Buffer
- (iii) Sound Buffers

These buffers are defined by registers in the DMA Address Generators, which are programmed by encoding the data in the address bus and performing a write operation with MEMC in Supervisor mode. Figure 6 shows how an address is calculated to store data in the Address Generator registers.



NOTES:

- (1) The Register value is calculated by dividing the Physical RAM address by 16.
- (2) The following side effects occur when the Sound buffer address generators are programmed:
 - Programming the Sstart register sets the Next Sound Buffer Valid flag.
 - Programming the Sptr register forces a sound buffer swap.

Figure 6: Programming the DMA Address Generator registers

NOTES:

- (i) The Address Generator works to a resolution of 16 bytes (the number of bytes fetched during a DMA operation), so all DMA buffers must start and end on 16 byte boundaries. The data stored in the Address Generator registers is calculated by dividing the appropriate Physical RAM address by sixteen
- (ii) When the Sound pointer register, Sptr, is programmed, no immediate value is specified. Instead, a Sound buffer swap is forced, copying the value from Sstart to Sptr, and resetting the Next Sound Buffer Valid flag. (see Section 6.7.3)
- (iii) The processor may write to the DMA registers at any time, but multiple, consecutive DMA register write operations (using the ARM Store Multiple instruction) should never be used, as this may inhibit the initialisation of the Video pointer register, Vptr. (see Section 6.7.5)
- (iv) The DMA Address generators are limited to addressing the bottom 512KBytes of Physical memory. However, the Logical to Physical Address Translator can be used make this 512KByte Physical address space appear anywhere in the processor's 32MByte Logical address space.

6.7.1 Video Buffer

This is a circular buffer, as shown in Figure 7. The buffer is a section of memory delimited by *Vstart* and *Vend* that contains all the Video data for a frame.

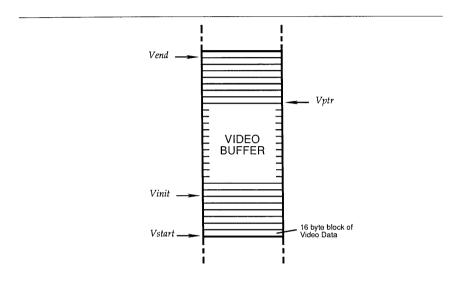


Figure 7: Circular Video Data Buffer

When a Video DMA is requested, the address held in *Vptr* (the <u>Video Pointer</u>) is used to obtain four consecutive 32-bit words of data (16 bytes) from the DRAM. The <u>VIDAK</u> line is strobed LOW as each word of data is read from the DRAM. The *Vptr* register is then incremented ready to point to the next four words of Video data, unless it has reached the end of the buffer (as delimited by *Vend*), in which case *Vptr* is reset to the start of the buffer (as defined by *Vstart*).

The *Vinit* register contains the address to which *Vptr* will be initialised just before the new display frame begins (denoted by a HIGH to LOW transition on **FLYBK**), and should be programmed with the address of the first byte of video data for the new frame. Hardware scrolling is effected by reprogramming *Vinit*.

The processor may program the *Vstart*, *Vinit* and *Vend* registers (provided MEMC is in Supervisor mode). The *Vptr* register cannot be altered directly by the processor, but is always reset to the value contained in *Vinit* before a new Video frame is displayed.

The Video Pointer register, *Vptr*, doubles as a refresh counter. When a refresh is performed, the *Vptr* address is output to the DRAMs, and *Vptr* is incremented to the next 16 byte boundary (no check is made that *Vptr* has reached the end of the buffer). As refresh operations alter the contents of *Vptr*, continous refresh must never be enabled while Video DMAs are operative.

6.7.2 Cursor Buffer

This is a linear buffer, and is shown in Figure 8. The cursor data is contained in a section of memory whose initial (low) address is stored in the *Cinit* register. While **FLYBK** is HIGH, *Cptr* (the Cursor Pointer) is initialised to the address held in *Cpit*. When a Cursor DMA is serviced, the address held in *Cptr* is sent to the DRAM, and used to obtain four consequtive 32-bit words of data (16 bytes). The *Cptr* is then incremented ready to point to the next four words of Cursor data.

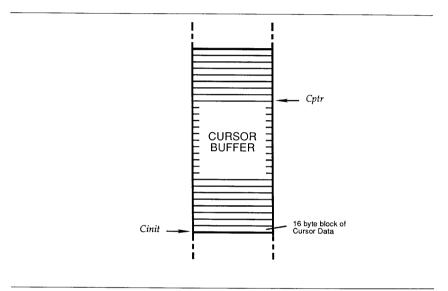


Figure 8: Linear Cursor Data Buffer

6.7.3 Sound Buffers

Sound data is divided into areas of memory called *sound buffers*. The sound system can support any number of sound buffers using the DMA Address Generators and interrupt driven software. Sound data is extracted from one buffer at a time, and when each buffer is exhausted, a new sound buffer is used.

The DMA Address Generators contain information on two sound buffers as follows (see Figure 9):

(i) Current Sound Buffer

This is the buffer from which sound data is extracted when a Sound DMA is requested. The address of the next 16 bytes of sound data to be supplied in response to a Sound DMA request is held in the Sound Pointer register, *Sptr*, and the end of the Current Buffer is delimited by the Current Sound End register, *SendC*.

(ii) Next Sound Buffer

This is the buffer of sound data which will be used once the Current Sound Buffer is exhausted. The Next Sound Buffer is defined by programming the *Sstart* and *SendN* registers. (NOTE: The processor can only ever program the start and end addresses of the Next Sound Buffer).

A hardware flag, Next Buffer Valid, is set when the Next Sound Buffer registers have been programmed.

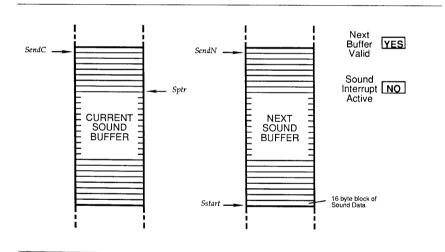


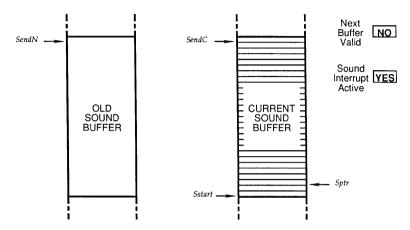
Figure 9: Current and Next Sound Buffers

Chapter 6

Sound Buffer operation

(1) Sound Buffer swap

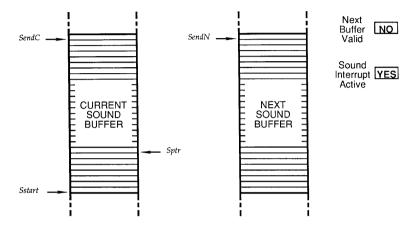
When Sptr reaches the end of the Current Buffer, it swaps to the start of the Next Buffer, provided the Next Buffer Valid flag is set.



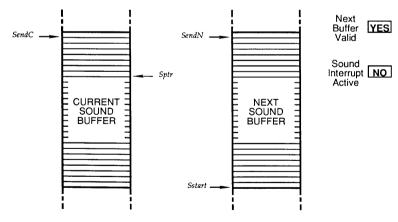
The buffer swap resets the Next Buffer Valid flag, and generates a sound interrupt by driving the SIRQ pin LOW. The SendC and SendN registers swap over, so that the value previously set up in SendN defines the end of the new Current Buffer.

(2) Next Sound Buffer setup

The processor should react to the sound interrupt by programming the start and end addresses for a buffer containing new sound data (the Next Sound Buffer). The first part of this process is to define the end address by reprogramming *SendN*.



The processor may now define the start address by reprogramming *Sstart*. This fully defines the Next Buffer, setting the Next Buffer Valid flag and driving **SIRQ** HIGH. The sequence of events now repeats from Step (1) again.



NOTE: If the processor fails to setup a new *Sstart* value before the Sound Pointer reaches the end of the Current Buffer, the Sound Pointer will jump back to the start of the Current Buffer (as defined by the old value of *Sstart*), thus repeating the last buffer of sound data.

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Functional Description

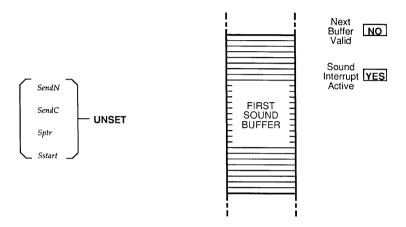
Initialising the Sound Buffers

The following procedure is recommended for initialising the Sound Buffers to a known state:

(1) Initial state

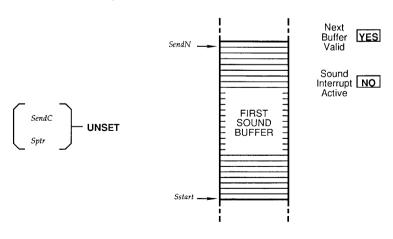
After reset Sound DMA operations are disabled. To start the sound system, the processor must first fill an area of memory with sound data; this will become the First Sound Buffer.

NOTE: The Sound Interrupt line, SIRQ, is set LOW when RESET is asserted.



(2) Defining the First Buffer

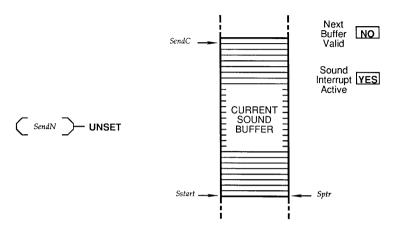
The SendN and Sstart registers are then programmed with the end and start addresses of the First Buffer. This drives SIRO HIGH.



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(3) Initialising the Sound Pointer

The Sound Pointer is now defined by performing a write operation to the Sptr register. Rather than defining an immediate value to be stored in Sptr, this operation forces a <u>buffer</u> swap, copying the contents of Sptr, swapping over SendN and SendC, and driving the \overline{SIRQ} pin LOW.



The processor may now enable Sound DMA operations by reprogramming the MEMC Control Register, and handle the sound interrupt in the usual way to set up the Next Buffer.

6.7.4 Processor/DMA memory arbitration

DMA operations read four words from the DRAM. The memory accesses are organised as an N-cycle followed by three S-cycles. As the DMA operation uses the system data bus, the processor must be prevented from performing memory accesses until the DMA has finished.

If both a DMA operation and a processor memory access cycle are pending, the DMA operation will normally have priority, and the processor will be disabled at the end of its current cycle until the DMA operation completes. However, processor S-cycle memory accesses (either to DRAM or nibble-mode ROM) have higher priority than DMA operations, and the DMA operation will be postponed until the processor stops performing S-cycles. Excessive DMA latency is avoided by limiting the maximum number of consecutive processor S-cycles to three.

Processor internal cycles may occur concurrently with DMA operations, but the processor will be disabled if it attempts any memory access cycle during DMA.

The processor is disabled at the start of a cycle by stopping the processor clocks with PH1 HIGH.

The DMA request may arrive while the processor is suspended awaiting the completion of an IO cycle. In this case, the IORQ signal is driven HIGH when REF8M next goes LOW. The DMA operation may then begin, and when it completes, the IO cycle is resumed by setting IORQ LOW again (provided no more DMA or refresh operations are pending).

The DBE line is always driven LOW during DMA operations to disable the processor data bus drivers.

6.7.5 DMA handshaking

A Sound DMA operation is requested by taking the SNDRO line LOW.

When the DMA operation is performed, the DRAM is accessed, and an acknowledge line, (either VIDAK for Video/Cursor DMA, or SNDAK for Sound DMA) is strobed low as each word of data becomes available on the data bus. The rising edge of VIDAK or SNDAK should be used to latch the DMA data from the data bus².

The appropriate DMA request line (VIDRQ or SNDRQ) should be taken HIGH when the first DMA acknowledge is given unless a consecutive DMA is to be performed.

The FLYBK signal prompts MEMC to initialise the Video and Cursor buffer pointers. The Cursor pointer is initialised during flyback, and the Video pointer is initialised just after FLYBK goes LOW. The initialisation of the Video pointer is left this late to allow it to be used as refresh pointer during flyback.

The VIDRQ, SNDRQ, HSYNC and FLYBK signals may be asynchronous, so they are all passed through two synchronisation latches in MEMC to avoid synchronisation failure.

Selecting Video or Cursor DMA operations

The \overline{HSYNC} signal determines whether a Video or Cursor DMA is to be performed, and is latched on the HIGH to LOW transition of \overline{VIDRQ} . The hold time on \overline{HSYNC} must be sufficient to allow the synchronisation latches in MEMC to capture its state.

When two or more Video/Cursor DMA operations occur consecutively, \overline{HSYNC} is sampled on the falling edge of the penultimate \overline{VIDAK} strobe, and its state at this point determines whether the next DMA operation will fetch Video or Cursor data.

The setup and hold requirements of HSYNC are given in Section 8.8.3.

DMA latencies

Video/Cursor DMA requests have a higher priority than Sound requests, and will always be serviced first.

The maximum DMA latency from the time a VIDRQ or SNDRQ line is taken low to the first 32-bits of DMA data being read from DRAM is as follows:

Video/Cursor DMA latency

VIDRQ passes through two synchronisation latches. The delay through these latches varies from approx 10ns to 125ns, depending on the relative phase of VIDRQ and the internal 8MHz synchronising clock. It then takes 187ns to process the Video request, and prepare to execute a DMA cycle. A further delay of 500ns may be incurred if the processor had just started a worst case uninterruptable DRAM access (N-cycle + three S-cycles with no internal cycles) in the preceding 8MHz internal clock cycle. Finally, it takes 250ns for the DRAM N-cycle read operation to supply the first word of video/cursor data.

Thus, the minimum and maximum delays from VIDRQ going LOW to the first word of data being available from the DRAMs are:

Minimum Video/Cursor DMA latency = 10+187+250 ≈450ns

Maximum Video/Cursor DMA latency = 125+187+500+250 ≈1070ns

(ii) Sound DMA latency

The Sound DMA latency is similar to the Video/Cursor DMA latency. However, Sound DMA operations have a lower priority than Video/Cursor DMA operations, and will be delayed by 625ns for every consecutive Video/Cursor DMA operation that is requested at the same time as, or after SNDRO goes LOW.

Thus, the minimum and maximum delays from SNDRQ going LOW to the first word of data being available from the DRAMs are:

Minimum Sound DMA latency = 10+187+250 ≈450ns

Maximum Sound DMA latency = 125+187+500+250+(625*DMA $_{V/C}$) $^{\approx}1070+(625*DMA_{V/C})$ ns

where $DMA_{V/C}$ is the maximum number of consecutive Video/Cursor DMA operations that may occur while the Sound DMA is pending.

Some DRAMs may disable their data bus drivers before the DMA acknowledge line goes IIIGII. In this case, the dynamic storage time of the data bus is normally sufficient to hold the data valid until it is latched.

Flyback requirements

The Video and Cursor buffer pointers must be reset between one video frame and the next.

The Cursor pointer is initialised during flyback (signalled by FLYBK HIGH). The initialisation takes 250ns and occurs provided that the following conditions are met:

- (i) **FLYBK** is HIGH (signalling that flyback is in operation).
 - It may take up to 250ns for MEMC to synchronise and process the LOW to HIGH transition of the FLYBK signal.
- (ii) The processor is performing a normal memory access (not an S-cycle), but is NOT writing to the DMA Address Generator or the MEMC Control Register.
- (iii) No DMA operation is in progress.
- (iv) No refresh operation is in progress.

NOTE: These conditions may be satisified many times during flyback, and the Cursor pointer will be initialised on each occasion. The **FLYBK** signal must remain HIGH long enough to initialise the Cursor pointer at least once.

The Video pointer is not reset until after FLYBK makes a transition from HIGH to LOW (the end of the flyback period). This allows the Video pointer to be used as a refresh address register during flyback. The initialisation takes 250ns and occurs provided that the following conditions are met:

- (i) FLYBK has made a transition from HIGH to LOW (signalling the end of flyback), and the Video pointer has not already been initialised since FLYBK made the transition.
 - It may take up to 250ns for MEMC to synchronise and process the HIGH to LOW transition of the FLYBK signal.
- (ii) The processor is performing a normal memory access (not an S-cycle), but is NOT writing to the DMA Address Generator or the MEMC Control Register.
- (iii) No DMA operation is in progress.
- (iv) No refresh operation is in progress.

The delay between FLYBK going LOW and the first Video DMA being processed must be long enough to allow the Video pointer to be reset.

6.8 Video Controller (VIDC) Interface

To program the VIDC Video Controller, the processor performs a write operation anywhere in the Video Controller address space while MEMC is in Supervisor mode. The Video Controller register number and data are encoded entirely in a 32-bit word which is available on the processor data bus during the write operation (see the VIDC Datasheet for more detail). MEMC provides a Video Controller Write signal, VIDW, that may be used to latch the information off the data bus.

6.9 I/O Controller Interface

I/O Controllers use a handshaking system to synchronise I/O peripherals with the system data bus. When the processor accesses the I/O Controller address space (while MEMC is in Supervisor mode), MEMC starts an IO cycle by driving the IO cycle request line, IORQ, LOW and holding the processor clocks (stretching the processor cycle when PH2 is HIGH). The I/O Controller signals that it is ready to end the IO cycle by driving the IO cycle grant line IOGT, LOW. The I cycle terminates after both IORQ and IOGT are seen LOW on the rising edge of REF8M, with MEMC driving IORQ HIGH and releasing the processor clocks, and the I/O Controller driving IOGT HIGH on the next falling edge of REF8M.

An IO cycle is shown if Figure 10. The cycle starts with \overline{IORQ} being taken low. There then follows a number of 8MHz clock ticks until the I/O Controller is in a position to complete the cycle. The \overline{IOGT} line is taken low, and both MEMC and the I/O controller see \overline{IORQ} and \overline{IOGT} LOW on the rising edge of REF8M, so the IO cycle terminates on the next falling edge of REF8M.

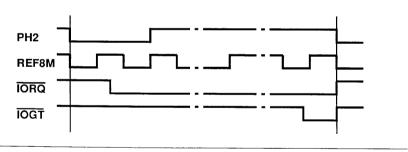


Figure 10: IO Cycle

IO cycles may be interrupted by \overline{DMA} and refresh operations, as shown in Figure 11. If a DMA or refresh operation is pending, the \overline{IORQ} signal is driven HIGH when **REF8M** next goes LOW. The \overline{DMA} /refresh operation may then begin, and when it completes, the IO cycle is resumed by setting \overline{IORQ} LOW (provided no more DMA or refresh operations are pending). The **DBE** line is always driven LOW during DMA/refresh operations to disable the processor data bus drivers.

NOTE: The I/O Controllers must not drive the data bus when \overline{IORQ} is HIGH.

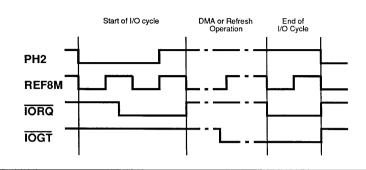


Figure 11: IO Cycle interrupted by a DMA or refresh operation

Some IO cycles may only take 250ns as shown in Figure 12. To give the Input/Output Controller adequate time to recognise such operations, MEMC produces the first $\overline{10RQ}$ early in the IO cycle.

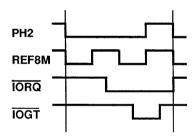


Figure 12: Fast IO cycle

The extension of \overline{IORQ} only happens at the start of an IO cycle; if the \overline{IORQ} signal is removed during a DMA or refresh operation, it will be reasserted when REF8M goes LOW.

NOTES: Care must be taken not to address a non-existent Input/Output Controller, as MEMC will hold the processor clocks indefinitely until a LOW is seen on the $\overline{\mathbf{10GT}}$ line, or RESET is set HIGH.

7. DC Parameters

7.1 Absolute Maximum Ratings

Symbol	Parameter	 Min 	Max	Units	 Note
VDD	 Supply voltage	VSS-0.3	VSS+7.0	v	1
Vip	Voltage applied to any pin	 VSS-0.3	VDD+0.3	V	1 1
Ts	 Storage temperature 	-40 	 125 	deg.C	! 1

NOTE:

(1) These are stress ratings only. Exceeding the absolute maximum ratings may permanantly damage the device. Operating the device at absolute maximum ratings for extended periods may affect device reliability.

7.2 DC Operating Conditions

Symbol	 Parameter 	 Min 	Typ	 Max 	 Units	Note
I VDD	Supply voltage	4.75	5.00	5.25	ı v	1
Vihc	 IC input HIGH voltage	3.5		VDD	 V	1,2
Vilc	IC input LOW voltage	0.0	1 	0.8	V	1,2
Ta 	 Ambient operating temperature 	 0 	 	 70 	 deg.C 	

NOTES:

- (1) Voltages measured with respect to VSS.
- (2) IC CMOS compatible inputs.

7.3 DC Characteristics

KEY

Mes - Values measured from a sample MEMC.

Nom - Nominal values derived from analogue simulations.

 Symbol	Parameter	 Mes 	Nom	Units	Note
IDD	Supply current	 		mA	
Isc	Output short circuit current	 >25		m A	1
 Ilu	D.C. latch-up current	300		mA	2
 Iinc	IC input leakage current	! !	10	u A	
Vohc	OC output HIGH voltage	1	4.2	ı V	3,6
Volc	OC output LOW voltage	[[0.3	 V	3,7
Voht	OT output HIGH voltage	!	3.7	V	4,8
Volt	 OT output LOW voltage	!	0.4	I I V	4,9
Vihet	 IC input HIGH voltage threshold	 	 2.8 	 V 	 5
Vilct	 IC input LOW voltage threshold	1 	 2.0) V 	 5
Cin	 Input capacitance 	 5 	! ! !	 pF 	

NOTES:

- (1) Not more than one output should be shorted to either rail at any time, and for no longer than 1 second.
- (2) This value represents the D.C. current that the input/output pins can tolerate before the chip latches up.
- (3) OC CMOS compatible outputs.
- (4) OT TTL compatible outputs.
- (5) IC CMOS compatible inputs.
- (6) Output current = 3mA
- (7) Output current = -3mA
- (8) Output current = 10mA
- (9) Output current = -10mA

8. AC Parameters

TEST CONDITIONS

The AC timing diagrams presented in this section assume that the outputs of MEMC have been loaded with the capacitive loads shown in the 'Test Load' column of Table 3; these loads have been chosen as typical of the type of system in which MEMC will be employed.

The output pads of MEMC are CMOS drivers which exhibit a propagation delay that increases linearly with the increase in load capacitance. An 'Output derating' figure is given for each output pad, showing the approximate increase in load capacitance necessary to increase the output time by one nanosecond.

Output Signal	Test Load (pF)	Output derating (pF/ns)	Note
PH1	15	5	1 1
PH2	15	5	1
DBE	20	 5	
ABORT	10	5	
IORQ	1 10	l ! 5	! !
REF8M	! 20	 5	l
RA[0:9]	 250	8	
RAS	 250	8	
CAS[0:3]	l 60	8	1
ROMCS	 40	l 5	
VIDW	1 10	 5	! !
VIDAK	1 10	 5	1
SNDAK	1 10	 5	1
SIRQ	 10 	 5 	İ

To maintain PH1/PH2 non-overlap, the capacitive load on PH1 and PH2 should not exceed 25pF.

Table 3: AC test loads

KEY TO TIMING TABLES

Sym - Symbol used in the timing diagrams.

Mes - Times measured in a sample ARM/MEMC/VIDC/IOC system running at 8MHz.

Nom - Nominal times.

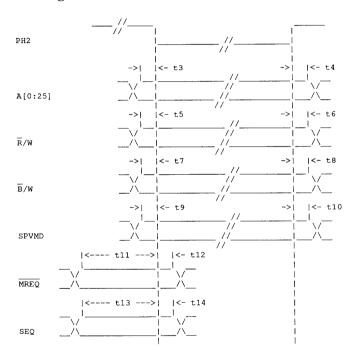
Lim - Times required to meet ARM/MEMC/VIDC/IOC system specifications.

AC Parameters

8.1 Input Clock



8.2 Processor Signals



Sym	Parameter	 Mes 	 Nom	 Lim 	Units	Note
t1	CK24M input clock HIGH	22	21	 	 ns	!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!!
t2	 CK24M input clock LOW 	20	! ! 21 !		ns	i i 1i

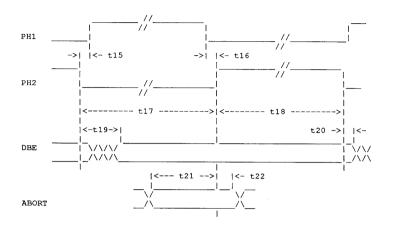
 Sym	Parameter	Mes	Nom	Lim	 Units	Note
t3	A[0:25] Address setup	0	0		ns	
 t4	A[0:25] Address hold	27	0		ns	
 t5	R/W setup	. 0	0	i L	ns	
 t6	R/W hold	l 33	0		ns ns	
 t7	 B/W setup	24	l 0	 	l ns	
 t8	 B/W hold	23	I ! 0	! !	ns	l
 t9	 SPVMD setup	l !	I I 0	! !	l ns	1 1
 t10	 SPVMD hold	1	0	1	ns	1 1
 t11	 MREQ setup	 100	l 75	 	ns	
 t12	 MREQ hold	 23	1 0	 	ns	
 t13	 SEQ setup	 70	l 75	 	ns	1
 t14 	 SEQ hold 	1 28 	 0 	 	 ns 	

NOTE:

(1) Transitions on SPVMD should normally occur only while PH2 is HIGH. If SPVMD changes during the PH2 LOW period of an access to a protected area of memory (including protected Logical pages), the access may not be allowed or aborted as expected.

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8.3 Processor Controls



		Ī	l	1	I	
Sym	Parameter	Mes	Nom	Lim	Units	Note
t15	PH2 to PH1 non-overlap	9	1 10	> 0	 ns	1
t16	PH1 to PH2 non-overlap	9	1 10	> 0	ns	1 1
t17	PH2 LOW period	1 196	187	1	ns	1 2
t18	PH2 HIGH period	54	62		ns	2
t19	PH2 LOW to DBE valid	5	0	ļ	ns	ĺ
t20	PH2 LOW to DBE invalid	5	0		ns	1
t21	ABORT to PH2 setup		80	> 35	ns	3
t22	ABORT to PH2 hold		1 10	> 0	ns	3

NOTES:

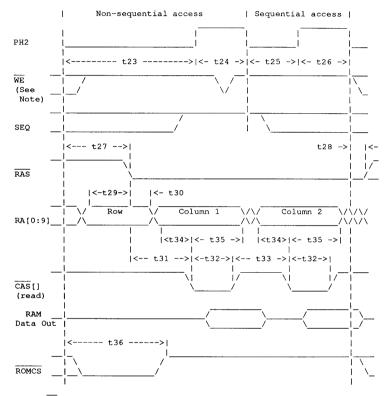
- (1) The ARM processor clocks must never overlap.
- (2) Most processor cycles take 250ns, with PH2 LOW for 187ns and HIGH for 62ns. The following exceptions apply:
 - Processor internal cycles take 125nS.
 - DRAM and nibble-mode ROM S-cycle memory accesses take 125ns.
 - ROM read operation cycle time is selectable, and may take 250ns, 375ns or 500ns.
 - The processor clocks are suspended during I/O cycles, with PH2 being held HIGH until the end of the I/O cycle.
 - PH2 may be held LOW during DMA and refresh operations.
- (3) The ABORT sctup and hold limits for the ARM processor were measured for a sample ARM. A factor of two should be allowed for process variations.

AC Parameters

Chapter 8

8.4 Processor accessing Dynamic RAM

8.4.1 Processor - Dynamic RAM read cycles



NOTE: $\overline{\text{WE}}$ is obtained by passing DBE through an external inverter.

MEMC Datasheet

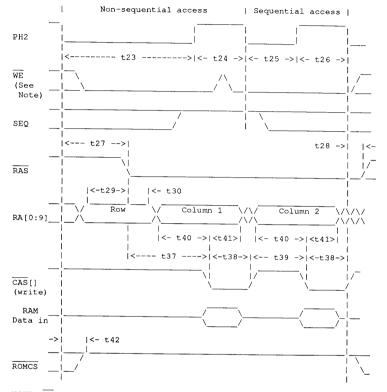
Sym	Parameter	Mes	Nom	Lim	Units	Note
t23	DRAM N-cycle:PH2 LOW	196	187		ns	
t24	DRAM N-cycle:PH2 HIGH	54	62		l ns	
t25	DRAM S-cycle:PH2 LOW	71	62	 	ns	
t26	DRAM S-cycle:PH2 HIGH	54	62	 	ns	
t27	RAS enable time	110	105	! !	ns	
t28	RAS disable time	8	0	! !	l ns	
t29	Row Address setup	93	1 40	 > 0	ns	1
t30	Row Address hold	26	 20	 > 15	l ns	1
t31	RAS to CAS[] enable (read)	58	l 62	> 25	ns	1
t32	CAS[] pulse width (read)	63	l ! 62	> 60	l ns	1
t33	CAS[] precharge period (read)	 60	 62	 > 50	l ns	1 1
t34	 Column Address setup (read)	13	20	 > 0	ns	1
t35	Column Address hold (read)	 89	 62	> 20	ns	1
t36	ROMCS disable time (read cycle)	 130 	 125 	1	 ns 	! !

NOTE:

(1) The DRAM timing limits are given for the particular DRAM used in the test system.

Chapter 8

AC Parameters



8.4.2 Processor - Dynamic RAM write cycles

NOTE: $\overline{\text{WE}}$ is obtained by passing DBE through an external inverter.

	Parameter	Mes	Nom	Lim	Units	Note
t23	DRAM N-cycle:PH2 LOW	196	187		ns	1
t24	DRAM N-cycle:PH2 HIGH	54	62		ns	
 t25	DRAM S-cycle:PH2 LOW	71	l 62	! !	l ns	
 t26	DRAM S-cycle:PH2 HIGH	54	62	i i	l ns	
 t27	RAS enable time	110	1 105	! !	l ns	İ
t28	RAS disable time	8	I I 0	! !	l ns	1
t29	Row Address setup	93	40	> 0	l ns	1 1
t30	Row Address hold	26	20	 > 15	l l ns	1 1
t37	RAS to CAS[] enable (write)	1 79	 83	 > 25	ns	1 1
t38	CAS[] pulse width (write)	63	62	 > 60	l ns	1
t39	CAS[] precharge period (write)	 60 	62 62	 > 25 	l ns 	 1
 t40	Column Address setup (write)	34	 40	 > 0	l ns	1 1
t41	Column Address hold (write)	 68	1 40	> 20	ns	1 1
t42 	ROMCS disable time (write cycle)	 5 	 0 	! ! !	 ns 	1

NOTE:

(1) The DRAM timing limits are given for the particular DRAM used in the test system.

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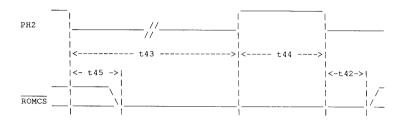
MEMC Datasheet

MEMC Datasheet

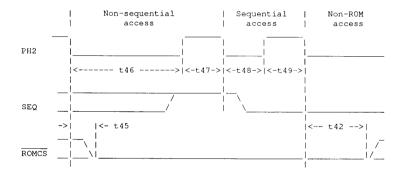
55

8.5 Processor accessing ROM

8.5.1 Non-sequential ROM access



8.5.2 Sequential ROM access (only with 200ns/60ns nibble-mode ROMs)



	Parameter	 Mes 	 Nom 	 Lim	 Units	
t42	ROMCS disable time	 5	0		ns	!
t43 l	200ns ROM read:PH2 LOW 325ns ROM read:PH2 LOW 450ns ROM read:PH2 LOW	196 320 445	187 312 437	 	ns ns ns	1 1 1
 t44	All ROM reads: PH2 HIGH	 54	 62	 	 ns]
t45	ROMCS enable time	5	0	İ	ns	i i
 t46	 200/60ns ROM N-cycle:PH2 LOW	 196	 187	 	 ns	
t47	200/60ns ROM N-cycle:PH2 HIGH	54	62	1	ns	i i
 t48	 200/60ns ROM S-cycle:PH2 LOW	71	 62	1	l l ns	
t49 	 200/60ns ROM S-cycle:PH2 HIGH 	54 54	 62 	! ! !	ns	

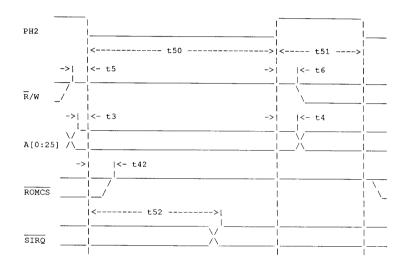
NOTE:

(1) The basic ROM access time is selectable as 200ns, 325ns or 450ns. PH2 is held LOW to extend the processor cycle, resulting in processor cycle times of 250ns, 375ns and 500ns respectively.

8.6 Processor accessing MEMC Internal Blocks

This timing diagram applies when the processor is writing to:

- (i) Logical to Physical Address Translator
- (ii) DMA Address Generators
- (iii) MEMC Control Register



	Parameter	 Mes 	Nom	Lim	 Units	Note
	A[0:25] Address setup	l I 0	 0	 	ns	
t4	A[0:25] Address hold	 27	 0		ns	
t5	R/W setup	 0	0		ns	
 t6	R/W hold	33	0		ns	
 t42 	ROMCS disable time (write cycle)	 5 	l 0 	 	 ns 	
 t50	MEMC write: PH2 LOW	 196	187		ns !	
t51	MEMC write: PH2 HIGH	 54	62		ns .	
 t52 	SIRQ enable/disable time	l 	 150 	 	 ns 	 1

NOTE:

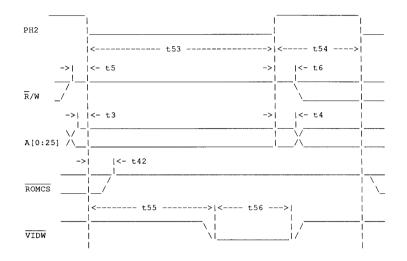
- (1) The \overline{SIRQ} interrupt is affected under the following circumstances:
 - The $\overline{\rm SIRQ}$ line is driven HIGH when the DMA Address Generator 'Sstart' register is programmed.
 - The SIRQ line is driven LOW when the DMA Address Generator 'Sptr' register is programmed.

MEMC Datasheet

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8.7 Processor accessing the Video Controller

This timing diagram applies when the processor performs a write operation to the Video Controller area of the memory map.



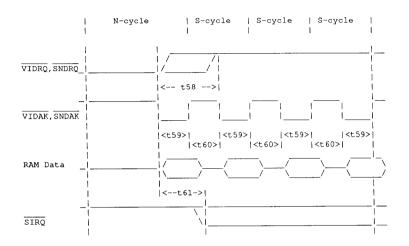
Sym	Parameter	Mes	Nom	Lim	Units	Note
t3	A[0:25] Address setup	0	0		ns	
t4	A[0:25] Address hold	27	0		ns	!
 t5	R/W setup	 0	l 0		ns	
 t6	_ R/W hold	33	0	 	l ns	
 t42 	ROMCS disable time (write cycle)	 5 	I I 0 I	! 	 ns 	
 t53 	 Video Controller write : PH2 LOW	 196	 187	 	l ns	
 t54 	 Video Controller write : PH2 HIGH	54	 62	! ! !	 ns	
 t55	PH2 LOW to VIDW enable	!	1 125	1	ns	1
 t56	VIDW pulse width	83 83	 83 	 > 20 	 ns 	i 1 i

NOTE:

(1) The VIDW pulse width limit was measured for a sample VIDC. A factor of two should be allowed for process variations.

8.8 Direct Memory Access (DMA) operations

8.8.1 DMA operation



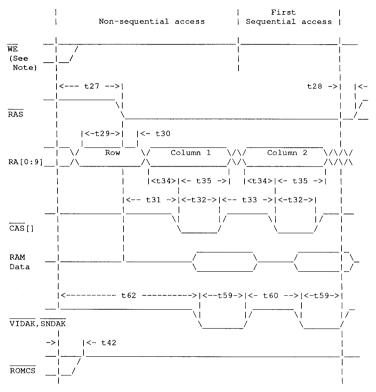
 Sym	Parameter	 Mes 	 Nom 	 Lim 	 Units 	
 t58	VIDRQ, SNDRQ disable time	 25	1	 <120	l l ns	
 t59	VIDAK, SNDAK pulse width	62	 62	> 15	l ns	1 2 1
t60	VIDAK, SNDAK pulse space	62	62	1	l ns	
 t61 	SNDAK to SIRQ active	 97 	 75 	! 	1 	3 3

NOTES:

- (1) If VIDRQ is not disabled within 120ns of VIDAK going LOW, a consecutive Video/Cursor DMA operation will result. Similarly, if SNDRQ is not disabled within 120ns of SNDAK going LOW, a consecutive Sound DMA operation will result.
- (2) The VIDAK and SNDAK pulse width limits were measured for a sample VIDC. A factor of two should be allowed for process variations.
- (3) The SIRQ interrupt will be set LOW during sound DMA operations where the Sound pointer swaps from the Current to the Next Sound Buffer.

Chapter 8

8.8.2 Direct Memory Access - Dynamic RAM read cycles



NOTE: $\overline{\text{WE}}$ is obtained by passing DBE through an external inverter.

Sym	Parameter	Mes	Nom	 Lim 	Units	Note
 t27	RAS enable time	110	105	l !	ns	
 t28	RAS disable time	8	 0	 	ns	
 t29	Row Address setup	93	40	> 0	l ns	1
t30	Row Address hold	26	1 20 :	 > 15	ns	1
 t31	RAS to CAS[] enable (read)	58	 62 :	 > 25	ns	1
 t32	CAS[] pulse width (read)	63	l 62	> 60	 ns	1 1
t33	CAS[] precharge period (read)	60	 62	 > 50	l l ns	1
 t34	Column Address setup (read)	13	l 20	> 0	l ns	1 1
 t35	Column Address hold (read)	89	 62	> 20	l ns	! 1
 t42 	ROMCS disable time (DMA cycle)	l l 5	 0 	 	 ns 	
 t59	VIDAK, SNDAK pulse width	62	 62	 > 15	l ns	1 2
 t60	VIDAK, SNDAK pulse space	l 62	l 62	1	l ns	! !
 t62 	VIDAK, SNDAK enable time	 188 	 187 	! ! !	 ns 	

NOTES:

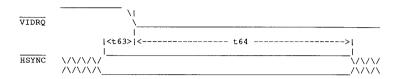
- (1) The DRAM timing limits are given for the particular DRAM used in the test system.
- (2) The VIDAK and SNDAK pulse width limits were measured for a sample VIDC. A factor of two should be allowed for process variations.

MEMC Datasheet

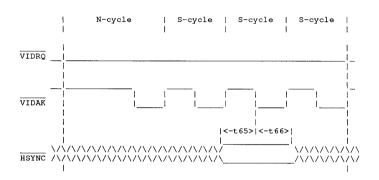
65

8.8.3 Selecting a Video or Cursor DMA

First Video/Cursor DMA request



Consecutive Video/Cursor DMA requests



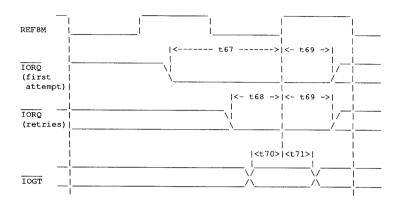
Sym	 Parameter 	 Mes 	Nom	 Lim 	Units	 Note
t63	HSYNC setup to VIDRQ active	 	20		 ns	l !
t64	HSYNC hold from VIDRQ active	! 	135	 	l ns	! !
t65	HSYNC setup for consecutive Video/Cursor DMA operations	! !	75		ns	
 t66 	HSYNC hold for consecutive Video/Cursor DMA operations	 	 20 	 	 ns]

Chapter 8

AC Parameters

8.9 I/O Controller Handshaking

This timing diagram applies when the processor accesses an I/O controller.

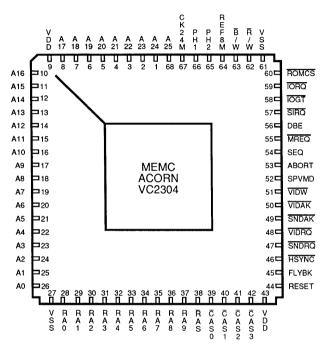


Parameter	 Mes 	 Nom 	 Lim 	 Units 	 Note
IORQ setup (first attempt)	110	l ! 90	[[l ns	
TORQ setup (retries)	62	1 50	 	l ns	! ! ! !
TORQ hold	 58	 50	! !	l i ns	! ! ! !
IOGT setup	!	! ! 30] -	l l ns	1
IOGT hold	1	1 10	1	l l ns	! ! ! !
	TORQ setup (first attempt) TORQ setup (retries) TORQ hold TOGT setup	10RQ setup (first attempt) 110 10RQ setup (retries) 62 10RQ hold 58 10GT setup 10RQ hold 10RQ ho		IORQ setup (first attempt)	IORQ setup (first attempt)

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9. Packaging

The device is packaged in a JEDEC B ceramic leadless chip carrier, or a JEDEC C plastic leaded chip carrier (PLCC).



Suitable sockets for the devices are:

- (i) AMP 55159-1 for the ceramic leadless chip carrier.
- (ii) Burndy QILE68P-410T for the plastic leaded chip carrier (PLCC).

Appendix A. RAM address bus

The RAM address bus, RA[0:9], as output from the DRAM Address Multiplexer is derived from three sources:

- (i) Processor address bus
- (ii) Logical to Physical Address Translator
- (iii) DMA Address Generators

During processor accesses to Physically mapped RAM, the higher order bits of the address bus, A[2:25], define the Physical page to be accessed, and the lower order bits define the word offset within that page. Similarly, when the processor accesses Logically mapped RAM, the Logical to Physical Address Translator supplies the Physical page number (provided that the access is successful). The row and column addresses supplied to the DRAM on RA[0:9] during processor accesses are a combination of the Physical page number (PPN[0:6]) and word offset (A[2:14]).

During DMA operations, the *DMA Address Generators* supply a 17-bit word address from which data is to be fetched. The DMA address is strobed to the DRAMs as a row and column address. The DMA Address Generators can only address 512kBytes, so the top bits of the address strobed to the DRAMs are padded with zeros to force the access in the bottom 512kBytes of memory.

Refresh operations use the address supplied by the Video pointer register in the DMA Address Generators.

The values output on the RAM address bus depend upon the Page size selected. Figure 13 shows the signal seen on RA[0:9] for each of the four Page sizes.

NOTES:

- (i) The outputs of the DRAM Address Multiplexer pass through inverting pads, so the signals seen on RA[0:9] are inverted.
- (ii) A[2:14] are 13-bits of the processor address bus that define the word offset within a Physical page.
- (iii) PPN[0:6] are 7-bits that define the Physical page number being accessed.
- (iv) DMA[2:18] are 17-bits from the DMA Address Generators that define the physical word address of a DMA read operation.

4NDY16	Page	Size			RAN	1 addres	s bus				
_		RA[9]	RA[8]	RA[7]	RA[6]	RA[5]	RA[4]	RA[3]	RA[2]	RA[1]	RA[0]
Processor	Row address	х	х	Ā[11]	Ā[10]	Ā[9]	Ā[8]	Ā[7]	Ā[6]	Ā[5]	Ā[4]
access	Column address	х	PPN[6]	PPN[5]	PPN[4]	PPN[3]	PPN[2]	PPN[1]	PPN[0]	A[3]	Ā[2]
DMA and	Row address	x	×	DMA[11]	DMA[10]	DMA[9]	DMA[8]	DMA[7]	DMA[6]	DMA[5]	DMA[4]
refresh operations	Column address	х	DMA[18]	DMA[17]	DMA[16]	DMA[15]	DMA[14]	DMA[13]	DMA[12]	DMA[3]	DMA[2]
8KByte	e Page	Size			RA	M addre	ss bus				
ſ	Row	RA[9]	RA[8]	RA[7]	RA[6]	RA[5]	RA[4]	RA[3]	RA[2]	RA[1]	RA[0]
Processor	address	Х	A[12]	A[11]	A[10]	A[9]	A[8]	A[7]	A[6]	A[5]	A[4]
access	Column address	Х	PPN[5]	PPN[4]	PPN[3]	PPN[2]	PPN[1]	PPN[0]	PPN[6]	A[3]	A[2]
DMA	Row	х	DMA[12]	DMA[11]	DMA[10]	[e]AMQ	DMA[8]	DMA[7]	DMA[6]	DMA[5]	DMA[4]
and refresh	address Column	×	DMA[18]			DMA[15]			1	DMA[3]	DMA[2]
operations	address		DIVIA(16)	DIVIA[17]	DIVIA(10)	DIVIA[15]	DIVIA[14]	DIVIA(13)	<u> </u>	DIVIA(0)	DIVIA(2)
16KBy	rte Pag	je Siz	е		RA	M addre	se hus				
						ivi audic	35 043				
	l Row	RA[9]	RA[8]	RA[7]	RA[6]	RA[5]	RA[4]	RA[3]	RA[2]	RA[1]	RA[0]
Processor	Row address	RA[9]	RA[8]	RA[7]	RA[6]			RA[3] A[7]	RA[2] A[6]	RA[1]	RA[0] ————————————————————————————————————
Processor access				Γ =	_	RA[5]	RA[4]		T =	T =	
	address Column	×	Ā[12] PPN[4]	Ā[11]	Ā[10]	RA[5] A[9] PPN[1]	RA[4] Ā[8]	Ā[7]	Ā[6]	Ā[5]	Ā[4]
DMA and refresh	address Column address Row address Column	X PPN[6]	Ā[12] PPN[4] DMA[12]	A[11] PPN[3] DMA[11]	Ā[10] PPN[2] DMA[10	RA[5] A[9] PPN[1]	RA[4] Ā[8] PPN[0] DMA[8]	Ā[7] Ā[13] DMA[7]	A[6] PPN[5] DMA[6]	Ā[5] Ā[3]	Ā[4] Ā[2]
DMA and refresh operations	address Column address Row address	X PPN[6] X	A[12] PPN[4] DMA[12] DMA[18]	A[11] PPN[3] DMA[11]	Ā[10] PPN[2] DMA[10	RA[5] Ā[9] PPN[1] DMA[9]	RA[4] A[8] PPN[0] DMA[8] DMA[14]	Ā[7] Ā[13] DMA[7]	A[6] PPN[5] DMA[6]	Ā[5] Ā[3] DMA[5]	Ā[4] Ā[2] DMĀ[4]
DMA and refresh operations	address Column address Row address Column address Column address	X PPN[6] X	A[12] PPN[4] DMA[12] DMA[18]	A[11] PPN[3] DMA[11]	Ā[10] PPN[2] DMA[10	RA(5) Ā[9] PPN[1] DMA[9] DMA[15]	RA[4] A[8] PPN[0] DMA[8] DMA[14]	Ā[7] Ā[13] DMA[7]	A[6] PPN[5] DMA[6]	Ā[5] Ā[3] DMA[5]	Ā[4] Ā[2] DMĀ[4]
DMA and refresh operations 32KBy	address Column address Row address Column address	x PPN[6] x 1	Ā[12] PPN[4] DMA[12] DMA[18]	Ā[11] PPN[3] DMA[11] DMA[17]	Ā[10] PPN[2] DMA[10 DMA[16	RA[5] A[9] PPN[1] DMA[9] DMA[15] M addre	RA[4] A[8] PPN[0] DMA[8] DMA[14]	Ā[7] Ā[13] DMA[7]	A[6] PPN[5] DMA[6]	Ā[5] Ā[3] DMĀ[5] DMĀ[3]	Ā[4] Ā[2] DMĀ[4] DMĀ[2]
DMA and refresh operations	address Column address Row address Column address /te Pac	X PPN(6) X 1 1 Qe Siz RA(9)	Ā[12] PPN[4] DMA[12] DMA[18]	Ā[11] PPN[3] DMA[11] DMA[17]	A[10] PPN[2] DMA[10 DMA[16 RA RA[6]	RA[5] Ā[9] PPN[1] DMA[9] DMA[15] M addre RA[5]	RA[4] A[8] PPN[0] DMA[8] DMA[14] Ess bus RA[4]	A[7] A[13] DMA[7] DMA[13	A[6] PPN[5] DMA[6] 1 RA[2]	Ā[5] Ā[3] DMA[5] DMA[3] RA[1]	Ā[4] Ā[2] DMA[4] DMA[2]
DMA and refresh operations 32KBy	address Column address Row address Column address /te Pac Row address Column address Column address Column	X PPN(6) X 1 Ge Siz RA(9) Ā(13) PPN(5)	PPN[4] DMA[12] DMA[12] DMA[18] PNA[8] Ā[12]	A[11] PPN[3] DMA[11] DMA[17] RA[7] A[11] PPN[2]	A[10] PPN[2] DMA[10 DMA[16 RA RA[6] A[10] PPN[1]	RA[5] Ā[9] PPN[1] DMA[9] DMA[15] M addre RA[5] Ā[9]	RA[4] Ā[8] PPN[0] DMĀ[8] DMĀ[14] SSS bus RA[4] Ā[8]	A[7] A[13] DMA[7] DMA[13 RA[3] A[7] PPN[6]	A[6] PPN[5] DMA[6] 1 RA[2] A[6] PPN[4]	A[5] A[3] DMA[5] DMA[3] RA[1] A[5] RA[3]	Ā[4]
DMA and refresh operations 32KBy	address Column address Row address Column address /te Pac Row address Column	X PPN(6) X 1 Ge Siz RA(9) Ā(13) PPN(5)	PPN[4] DMA[12] DMA[12] DMA[18] PNA[8] Ā[12]	A[11] PPN[3] DMA[11] DMA[17] RA[7] A[11] PPN[2]	A[10] PPN[2] DMA[10 DMA[16 RA RA[6] A[10] PPN[1]	RA(5) Ā[9] PPN[1] DMA[9] DMA(15) M addre RA(5) Ā[9]	RA[4] Ā[8] PPN[0] DMA[8] DMA[14] Ess bus RA[4] Ā[8]	A[7] A[13] DMA[7] DMA[13 RA[3] A[7] PPN[6]	A[6] PPN[5] DMA[6] 1 RA[2] A[6] PPN[4]	Ā[5] Ā[3] DMA[5] DMA[3] RA[1] Ā[5]	Ā[4]

Figure 13: RAM address bus signals

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